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Total No. of Questions: 18

B.Tech. (ECE) (Sem.-7) CMOS BASED DESIGN Subject Code: BTEC-908 M.Code: 71912

Time: 3 Hrs. Max. Marks: 60

INSTRUCTIONS TO CANDIDATES:

- 1. SECTION-A is COMPULSORY consisting of TEN questions carrying TWO marks each.
- 2. SECTION-B contains FIVE questions carrying FIVE marks each and students have to attempt any FOUR questions.
- 3. SECTION-C contains THREE questions carrying TEN marks each and students have to attempt any TWO questions.

SECTION-A

Write briefly:

- 1) Design a 3 input NOR gate using CMOS inverter.
- 2) Explain pull-up and pull-down networks for CMOS logic.
- 3) Draw drain current vs. voltage chart for MOS transistor.
- 4) Give the steps of CMOS processing.
- 5) Define photolithography.
- 6) Define propagation delay time.
- 7) What do you mean by linear delay model?
- 8) Define circuit family.
- 9) Explain glitching transitions.
- 10) Define the term sizing.

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SECTION-B

- 11) Give various design layout rules.
- 12) Explain the process of Photo masking with a negative resist.
- 13) Enlist the advantages and disadvantages of scaling.
- 14) Using static CMOS, design Bubble pushing to convert ANDs and ORs to NANDs and NORs.
- 15) Explain the optimization of Domino logic.

SECTION-C

- 16) Explain all the steps of fabrication process with diagrams.
- 17) Explain Gate and shallow source/drain formation.
- 18) Explain transistor and interconnect scaling.

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NOTE: Disclosure of Identity by writing Mobile No. or Making of passing request on any page of Answer Sheet will lead to UMC against the Student.

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